

	<u>Type</u>	<u>L #</u>	<u>Hits</u>	<u>Search Text</u>	<u>DBs</u>
<u>1</u>	<u>IS&R</u>	<u>L1</u>	<u>10</u>	<u>((("4,047,435") or ("4,896,196") or ("5,049,961") or ("5,119,265") or ("5,726,481") or ("6,268,986") or ("6,291,826") or ("6,342,997") or ("6,363,490") or ("20040017437"))).PN.</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>2</u>	<u>BRS</u>	<u>L2</u>	<u>5336</u>	<u>temperature adj2 sensing adj2 (devices or device)</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>3</u>	<u>BRS</u>	<u>L3</u>	<u>180</u>	<u>2 and (cathode near10 anode)</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>4</u>	<u>BRS</u>	<u>L4</u>	<u>102</u>	<u>3 and (diode or diodes)</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>5</u>	<u>BRS</u>	<u>L5</u>	<u>11</u>	<u>4 and ((semiconductor or silicon) adj2 (substrate))</u>	<u>US-PGPUB;</u> <u>USPAT</u>
<u>6</u>	<u>BRS</u>	<u>L6</u>	<u>1768</u>	<u>temperature adj2 sensing adj2 (devices or device)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>7</u>	<u>BRS</u>	<u>L7</u>	<u>38</u>	<u>6 and (cathode near10 anode)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>

	<u>Type</u>	<u>L #</u>	<u>Hits</u>	<u>Search Text</u>	<u>DBs</u>
<u>8</u>	<u>BRS</u>	<u>L8</u>	<u>18</u>	<u>7 and (diode or diodes)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>9</u>	<u>BRS</u>	<u>L9</u>	<u>50211</u>	<u>sensing adj2 (devices or device)</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>10</u>	<u>BRS</u>	<u>L10</u>	<u>1683</u>	<u>9 and (cathode near10 anode)</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>11</u>	<u>BRS</u>	<u>L11</u>	<u>1104</u>	<u>10 and (diode or diodes)</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>12</u>	<u>BRS</u>	<u>L12</u>	<u>82</u>	<u>11 and ((semiconductor or silicon)</u> <u>adj2 (substrate))</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>13</u>	<u>BRS</u>	<u>L13</u>	<u>26497</u>	<u>sensing adj2 (devices or device)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>14</u>	<u>BRS</u>	<u>L14</u>	<u>668</u>	<u>13 and (cathode near10 anode)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>

	<u>Type</u>	<u>L #</u>	<u>Hits</u>	<u>Search Text</u>	<u>DBs</u>
<u>15</u>	<u>BRS</u>	<u>L15</u>	<u>391</u>	<u>14 and (diode or diodes)</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>16</u>	<u>BRS</u>	<u>L16</u>	<u>2</u>	<u>15 and ((semiconductor or silicon)</u> <u>adj2 (substrate))</u>	<u>USOCR;</u> <u>EPO;</u> <u>JPO;</u> <u>DERWE</u> <u>NT;</u> <u>IBM TD</u> <u>B</u>
<u>17</u>	<u>IS&R</u>	<u>L17</u>	<u>461</u>	<u>(257/467).CCLS.</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>18</u>	<u>IS&R</u>	<u>L19</u>	<u>515</u>	<u>(257/659).CCLS.</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>
<u>19</u>	<u>IS&R</u>	<u>L18</u>	<u>142</u>	<u>(257/470).CCLS.</u>	<u>US-</u> <u>PGPUB;</u> <u>USPAT</u>